

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2100	(laser near (annealing annealed)) near1 (process method substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 15:48
L2	1	1 with (gate near (region dielectric)) with (("source/drain" (source near drain)) near1 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 15:38
L3	7540	(laser near (annealing annealed))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 15:48
L4	10	3 with (gate near (region dielectric)) with (("source/drain" (source near drain)) near1 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 15:40
L5	11	3 with (gate near (region dielectric)) with ("source/drain" (source near drain))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 15:39
L6	16	3 with (gate near (insulative insulation region dielectric)) with (("source/drain" (source near drain)) near1 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 15:48
L7	8013	(laser near (anneal annealing annealed))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:51
L8	18	7 with (gate near (insulative insulation region dielectric)) with (("source/drain" (source near drain)) near1 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:29
L9	32	"5518940"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:27

L10	45	"5523257"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:28
L11	37	"5563427"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:28
L12	50	"5620905"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:28
L13	21	"6307214"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:28
L14	18	"5474940"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:28
L15	189	9 10 11 12 13 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:28
L16	133	15 and laser	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 16:28
L17	124	16 and (anneal annealing annealed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 18:36
L18	65	17 and (gate near (metal electrode insulative insulation region dielectric)) with (("source/drain" (source near drain)) near1 region)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:18
L19	59	18 and metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:09

L20	2	8 and 19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:09
L21	75	8 19	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:27
L22	0	21 and (electron near volt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:10
L23	504	(work near function) with (electron near volt)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:10
L24	190	23 with metal	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:11
L25	29	24 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:11
L26	6	17 and (metal near gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:19
L27	26	21 and (implated implanting)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:48
L28	1	21 and (laser near4 (implated implanting))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:49
L29	6	21 and (laser with (implated implanting))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:49

L30	8919	(laser near2 (anneal annealing annealed))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:51
L31	74	30 and ((gate near1 (oxide insulative insulation dielectric)) near3 metal)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:53
L32	36	30 and ((gate near1 (oxide insulative insulation dielectric)) near3 (metal near layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:54
L33	36	30 and ((gate near1 (oxide insulative insulation dielectric)) near3 (metal near1 layer))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 17:54
L34	17	25 and (anneal annealing annealed)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2005/05/30 18:36